



FQD13N10LTM Information



For Reference Only

Part Number FQD13N10LTM

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 10A DPAK **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQD13N10LTM Specifications

Manufacturer Part Number FQD13N10LTM Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 12nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 520pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 40W (Tc) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds520pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 40W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
Technology Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs 12nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 520pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Series	QFET?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature Supplier Device Package Package / Case 10A (Tc) 12D (C 10) 5V 12D (C 5	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds520pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 40W (Tc)Rds On (Max) @ Id, Vgs180 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As a constance (Max) Poperating Temperature Supplier Device Package Package / Case 2 V @ 250μA 12nC @ 5V 12nC	Current - Continuous Drain (Id) @ 25°C	10A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 520pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 520pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 40W (Tc) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) ± 20 VFET Feature-Power Dissipation (Max) 2.5 W (Ta), 40 W (Tc)Rds On (Max) @ Id, Vgs 180 mOhm @ 5 A, 10 VOperating Temperature -55° C $\sim 150^{\circ}$ C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / Case $TO-252-3$, $DPak$ (2 Leads + Tab), $SC-63$	Gate Charge (Qg) (Max) @ Vgs	12nC @ 5V
FET Feature - Power Dissipation (Max) 2.5W (Ta), 40W (Tc) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	520pF @ 25V
Power Dissipation (Max) 2.5W (Ta), 40W (Tc) Rds On (Max) @ Id, Vgs 180 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs180 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	2.5W (Ta), 40W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	180 mOhm @ 5A, 10V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

FQD13N10LTM Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQD13N10LTM Payment Methods



















FQD13N10LTM Shipping Methods













If you have any question about FQD13N10LTM, please do not hesitate to contact us!

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